<b>PCN Number:</b> 201804160	00	PCN Date:	April	l 18, 2018	
Title: Datasheet for DRV110					
<b>Customer Contact:</b> PCN Manage	<u>er</u>		De	<b>ept:</b> Quality Service	ces
Change Type:					
Assembly Site	Design			Wafer Bump Site	
Assembly Process	□ Data She			Wafer Bump Material	
Assembly Materials	Part num	ber change		Wafer Bump Process	
Mechanical Specification	Test Site			Wafer Fab Site	
Packing/Shipping/Labeling	Test Prod	ess		Wafer Fab Materials	
				Wafer Fab Process	
	<b>Notificati</b>	on Details			
Description of Change:					
Texas Instruments Incorporated is a	announcing a	n information	only n	otification.	
The product datasheet(s) is being u	•		ow.		
The following change history provid-	es further de	tails.			
Texas Instruments					DV440
INSTRUMENTS SI VSRASG_MARCH				L BA8G -MARCH 2012-REVISED MA	RCH 2018
Changes from Revision F (March 2017) to F	Revision G		-		Page
Changed the maximum supply limited by the Changed the maximum supply limited by the change of t					
<ul> <li>Deleted virtual from the operating junction Absolute Maximum Ratings table</li> </ul>					
<ul> <li>Added the temperature range for the parameter, and updated the V<sub>IN</sub> and I<sub>Q</sub> parameter.</li> </ul>	meters in the Re	commended Opera	ating Con	nditions table, add the V <sub>S</sub>	
Deleted the solenoid inductance paramete					
<ul> <li>Deleted the I<sub>VIN</sub> test condition from the gat</li> </ul>	e drive voltage p	arameter in the Ele	ectrical C	Characteristics table	6
<ul> <li>Changed the parameter names for V<sub>PEAK</sub> a</li> </ul>					
<ul> <li>Added the input pulldown resistance parar</li> </ul>					
Added the DRV110 Current Control with V					
<ul> <li>Changed the R<sub>PEAK</sub> value for I<sub>PEAK</sub> = 450 m</li> <li>Changed the Configuring Peak and Hold 0</li> </ul>					n 10
is now named I <sub>PEAK</sub> and I <sub>HOLD</sub> settings for I	$R_{SENSE} = 1 \Omega$	and FEAR and HO	LD MODE	e v <sub>REF</sub> Settings image (which	11
<ul> <li>Changed the Voltage Supply and Integrate</li> </ul>	ed Zener Diode s	ection. Added the	VZENER V	falue table and changed the	1
R <sub>8</sub> equation to specify calculations for R <sub>8,n</sub>					
<ul> <li>Deleted the Default Configuration schematic</li> <li>Added the Current Limiting Resistor Selection and Passives Selection sections in the Detailed Design Procedure</li> </ul>					
<ul> <li>Changed the value of R<sub>PEAK</sub> from 303 kΩ to 400 kΩ in the Application Curve</li> </ul>					
The datasheet number will be chang	ging.				
Device Family	Ch	ange From:		Change To:	
DRV110	SL	VSBA8F		SLVSBA8G	
These changes may be reviewed at	the datashee	t links provide	ad .		
,		e mino provide	.u.		
http://www.ti.com/product/DRV110	<u>l</u>				
Reason for Change:					
To accurately reflect device characte	eristics.				
Anticipated impact on Fit, Form,	Function, (	uality or Re	liabilit	y (positive / negative	/e):
No anticipated impact. This is a spec		-			
to the actual device.				·	
Changes to product identificatio	n resulting	from this PC	N:		
None.					
Product Affected:					
DRV110APWR DRV110PW					

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com